# Quad 3-State Noninverting Buffers

## High-Performance Silicon-Gate CMOS

The 74HC125 is identical in pinout to the LS125. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

The HC125 noninverting buffer is designed to be used with 3-state memory address drivers, clock drivers, and other bus-oriented systems. The device has four separate output enables that are active-low.

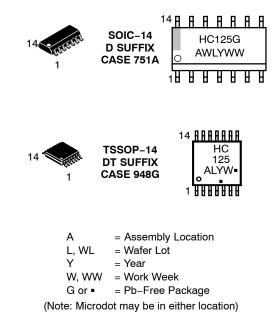
#### Features

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 µA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the JEDEC Standard No. 7A Requirements
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: 72 FETs or 18 Equivalent Gates
- These are Pb–Free Devices



http://onsemi.com

#### MARKING DIAGRAMS



**ORDERING INFORMATION** 

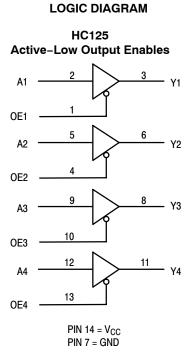
See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

#### **PIN ASSIGNMENT**

OE1 [	1•	14	v <sub>cc</sub>
A1 [	2	13	0E4
Y1 [	3	12	<b>A</b> 4
0E2 [	4	11	] Y4
A2 [	5	10	D OE3
Y2 [	6	9	] A3
GND [	7	8	D Y3

#### FUNCTION TABLE

HC125					
Inp	Output				
Α	OE	Y			
н	L	н			
L	L	L			
Х	Н	Z			



#### MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	– 0.5 to + 7.0	V
V <sub>in</sub>	DC Input Voltage (Referenced to GND)	$-0.5$ to $V_{CC}$ + 0.5	V
Vout	DC Output Voltage (Referenced to GND)	$-$ 0.5 to V_{CC} + 0.5	V
l <sub>in</sub>	DC Input Current, per Pin	±20	mA
I <sub>out</sub>	DC Output Current, per Pin	±35	mA
ICC	DC Supply Current, V <sub>CC</sub> and GND Pins	±75	mA
PD	Power Dissipation in Still Air SOIC Package† TSSOP Package†	500 450	mW
T <sub>stg</sub>	Storage Temperature	– 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (SOIC or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq (V_{in} \text{ or } V_{out}) \leq V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Derating — SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Max	Unit	
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)			6.0	V
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)		0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature, All Package Types		- 55	+ 125	°C
t <sub>r</sub> , t <sub>f</sub>		4.5 V	0 0 0	1000 500 400	ns

#### DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V <sub>CC</sub> (V)	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
VIH	Minimum High-Level Input Voltage	$V_{out} = V_{CC} - 0.1 V$	2.0	1.5	1.5	1.5	V
		$ I_{out}  \le 20 \mu A$	3.0	2.1	2.1	2.1	
			4.5	3.15	3.15	3.15	
			6.0	4.2	4.2	4.2	
VIL	Maximum Low-Level Input Voltage	$V_{out} = 0.1 V$	2.0	0.5	0.5	0.5	V
		$ I_{out}  \le 20 \ \mu A$	3.0	0.9	0.9	0.9	
			4.5	1.35	1.35	1.35	
			6.0	1.8	1.8	1.8	
V <sub>OH</sub>	Minimum High-Level Output	$V_{in} = V_{IH}$	2.0	1.9	1.9	1.9	V
	Voltage	$ I_{out}  \le 20 \ \mu A$	4.5	4.4	4.4	4.4	
			6.0	5.9	5.9	5.9	
		$V_{in} = V_{IH}$ $ I_{out}  \le 3.6 \text{ mA}$	3.0	2.48	2.34	2.2	
		$ I_{out}  \le 6.0 \text{ mA}$	4.5	3.98	3.84	3.7	
		$ I_{out}  \le 7.8 \text{ mA}$	6.0	5.48	5.34	5.2	
V <sub>OL</sub>	Maximum Low-Level Output	$V_{in} = V_{IL}$	2.0	0.1	0.1	0.1	V
	Voltage	$ I_{out}  \le 20 \ \mu A$	4.5	0.1	0.1	0.1	
			6.0	0.1	0.1	0.1	
		$V_{in} = V_{IL}$ $ I_{out}  \le 3.6 \text{ mA}$	3.0	0.26	0.33	0.4	
		$ I_{out}  \le 6.0 \text{ mA}$	4.5	0.26	0.33	0.4	
		$ I_{out}  \le 7.8 \text{ mA}$	6.0	0.26	0.33	0.4	
l <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	6.0	±0.1	±1.0	±1.0	μA
I <sub>OZ</sub>	Maximum Three-State Leakage	Output in High-Impedance State	6.0	±0.5	±5.0	±10	μΑ
	Current	$V_{in} = V_{IL} \text{ or } V_{IH}$					
		V <sub>out</sub> = V <sub>CC</sub> or GND					
Icc	Maximum Quiescent Supply Current	V <sub>in</sub> = V <sub>CC</sub> or GND	6.0	4.0	40	40	μΑ
	(per Package)	$I_{out} = 0 \ \mu A$					

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

## 74HC125

			Gu	Guaranteed Limit		
Symbol	Parameter	V <sub>CC</sub> (V)	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
t <sub>PLH</sub> ,	Maximum Propagation Delay, Input A to Output Y	2.0	90	115	135	ns
t <sub>PHL</sub>	(Figures 1 and 3)	3.0	36	45	60	
		4.5	18	23	27	
		6.0	15	20	23	
t <sub>PLZ</sub> ,	Maximum Propagation Delay, Output Enable to Y	2.0	120	150	180	ns
t <sub>PHZ</sub>	(Figures 2 and 4)	3.0	45	60	80	
		4.5	24	30	36	
		6.0	20	26	31	
t <sub>PZL</sub> ,	Maximum Propagation Delay, Output Enable to Y	2.0	90	115	135	ns
t <sub>PZH</sub>	(Figures 2 and 4)	3.0	36	45	60	
		4.5	18	23	27	
		6.0	15	20	23	
t <sub>TLH</sub> ,	Maximum Output Transition Time, Any Output	2.0	60	75	90	ns
t <sub>THL</sub>	(Figures 1 and 3)	3.0	22	28	34	
		4.5	12	15	18	
		6.0	10	13	15	
C <sub>in</sub>	Maximum Input Capacitance	-	10	10	10	pF
C <sub>out</sub>	Maximum 3-State Output Capacitance (Output in High-Impedance State)	-	15	15	15	pF

#### **AC ELECTRICAL CHARACTERISTICS** ( $C_L = 50 \text{ pF}$ , Input $t_r = t_f = 6.0 \text{ ns}$ )

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

C <sub>PD</sub> Power Dissipation Capacitance (Per Buffer)* 30 pF			Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
	C <sub>PD</sub>	Power Dissipation Capacitance (Per Buffer)*	30	pF

\* Used to determine the no-load dynamic power consumption: P<sub>D</sub> = C<sub>PD</sub> V<sub>CC</sub><sup>2</sup>f + I<sub>CC</sub> V<sub>CC</sub>. For load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

#### ORDERING INFORMATION

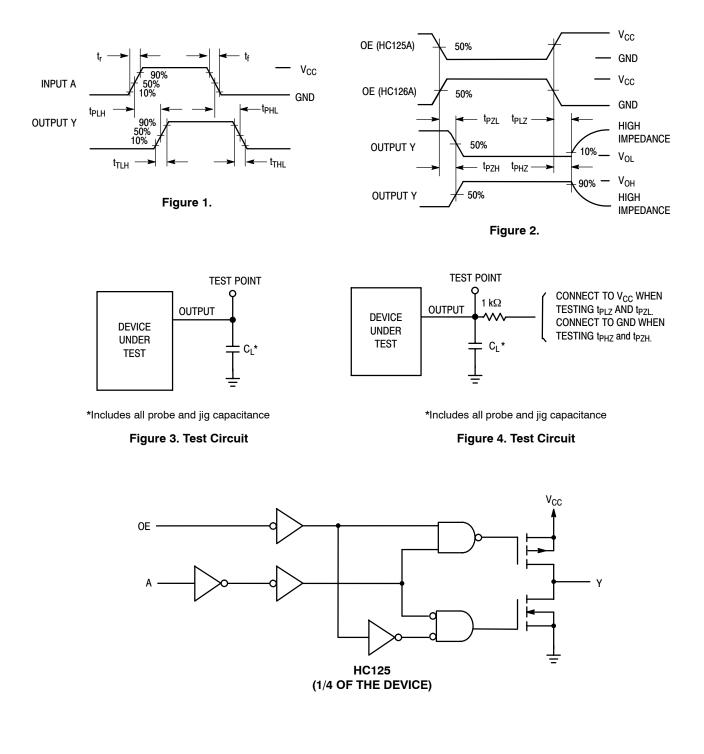
Device	Package	Shipping <sup>†</sup>
74HC125DR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
74HC125DTR2G	TSSOP-14*	2500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*This package is inherently Pb-Free.

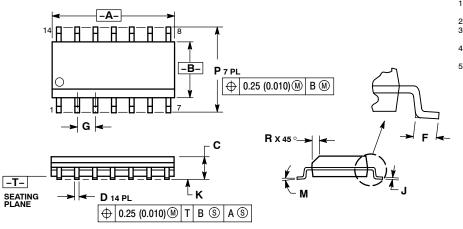
## 74HC125

### SWITCHING WAVEFORMS



#### **PACKAGE DIMENSIONS**

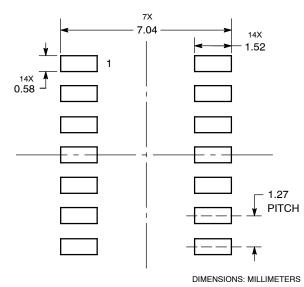
SOIC-14 CASE 751A-03 **ISSUE H** 



- NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER. 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION. 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE. 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
κ	0.10	0.25	0.004	0.009
м	0 °	7 °	0 °	7 °
Р	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

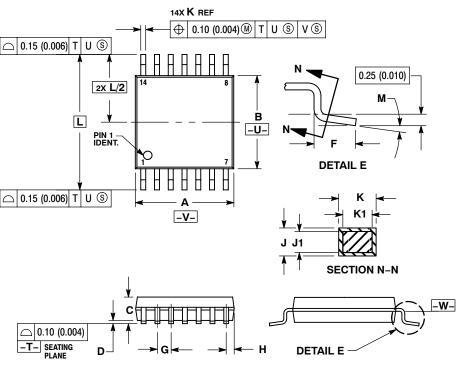
#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### PACKAGE DIMENSIONS

TSSOP-14 CASE 948G-01 **ISSUE B** 

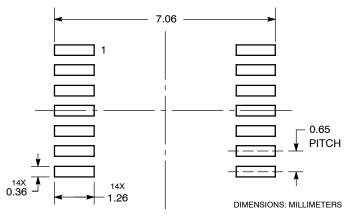


NOTES: 1. DIMENSIONING AND TOLERANCING PER

 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
CONTROLLING DIMENSION: MILLIMETER.
DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. SHALL NOT EXCEED 0.25 (0.010) PER SIDE. NOT EXCEED 0.25 (0.010) PER SIDE. 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY. 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026	BSC
н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
К	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40	BSC	0.252 BSC	
М	0 °	8 °	0 °	8 °

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### 74HC125

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